

DSC180N75ZE

Silicon Carbide MOSFET 750V, 180mΩ, 20A



重庆平伟半导体股份有限公司

Features

- 0 V turn-off gate voltage can be applied
- High Blocking Voltage with Low RDS(on)
- High Speed Switching with Low Capacitances
- Easy to Parallel and Simple to Drive
- Qualified according to JEDEC criteria

Applications

- Lighting
- Telecom and UPS
- PWM stages for e.g. PC Silverbox, Adapter, LCD & PDP TV

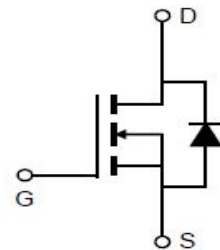
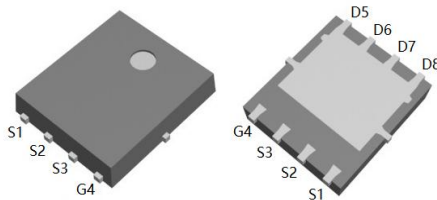


100% DVDS Tested
100%
Avalanche Tested

Product Summary

V _{DS}	750V
R _{DS(on)} typ.	180mΩ
I _D	20A

PDFN5*6



Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
DSC180N75ZE	DSC180N75ZE	PDFN5*6	Tape&Reel	13 inches	12mm	5000pcs

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V _{DS}	750	V
Continuous drain current	I _D	20	A
T _C = 25°C		14	
T _C = 100°C			
Pulsed drain current (T _C = 25°C)	I _{D pulse}	59	A
Avalanche energy, single pulse (L=5mH)	E _{AS}	16	mJ
Gate-Source voltage,max.transient voltage	V _{GSmax}	-8/+22	V
Recommended operating values	V _{GSsop}	0/+18	V
Power dissipation	P _{tot}	76	W
T _C = 25°C			
Operating junction and storage temperature	T _j , T _{stg}	-55...+175	°C

Thermal Resistance

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Thermal resistance, junction – case.	R_{thJC}	-	1.3	2.0	°C/W	-
Thermal resistance, junction - ambient(min. footprint)	R_{thJA}	-	-	50	°C/W	1 inch ² , 2oz single copper FR-4 PCB.

Electrical Characteristic (at T_j = 25 °C, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

Static Characteristic

Drain-source breakdown voltage	BV_{DSS}	750	-	-	V	$V_{GS}=0V, I_D=100\mu A$
Gate threshold voltage	$V_{GS(th)}$	2.5	3.5	4.5	V	$V_{DS}=V_{GS}, I_D=6mA$
Zero gate voltage drain current	I_{DSS}	-	1	10	μA	$V_{DS}=750V, V_{GS}=0V$ $T_j=25^\circ C$
		-	-	100		$T_j=175^\circ C$
Gate-source leakage current	I_{GSS}	-	-	100	nA	$V_{GS}=22V, V_{DS}=0V$
		-	-	-100	nA	$V_{GS}=-8V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	180	240	mΩ	$V_{GS}=15V, I_D=10A$
Drain-source on-state resistance	$R_{DS(on)}$	-	130	185	mΩ	$V_{GS}=18V, I_D=10A$
Transconductance	g_{fs}	-	6.5	-	S	$V_{DS}=20V, I_D=10A$

Dynamic Characteristic

Input Capacitance	C_{iss}	-	503	-	pF	$V_{GS}=0V, V_{DS}=400V,$ $f=1MHz$
Output Capacitance	C_{oss}	-	42	-		
Reverse Transfer Capacitance	C_{rss}	-	4	-		
Gate Total Charge	Q_G	-	17	-	nC	$V_{DS}=400V, I_D=10A$ $, V_{GS}=0V/15V$
Gate-Source charge	Q_{gs}	-	5	-		
Gate-Drain charge	Q_{gd}	-	8	-		
Turn-on delay time	$t_{d(on)}$	-	12	-	ns	$V_{GS}=0/18V, V_{DD}=400V,$ $R_G=5\Omega, I_D=10A$
Rise time	t_r	-	13	-		
Turn-off delay time	$t_{d(off)}$	-	22	-		
Fall time	t_f	-	7	-		
Gate resistance	R_G	-	3.0	-	Ω	$V_{GS}=0V, f=1MHz$

Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	-	4.2	-	V	$V_{GS}=0V, I_{SD}=10A$ $T_j=25^{\circ}C$
		-	3.7	-		$T_j=175^{\circ}C$
Body Diode Continuous Forward Current	I_S	-	-	18	A	$T_C = 25^{\circ}C$
		-	-	13	A	$T_C = 100^{\circ}C$
Body Diode Reverse Recovery Time	t_{rr}	-	23	-	ns	$V_{GS}=-5V, I_{SD}=10A,$ $V_R=400V$ $di/dt=1000A/us$
Body Diode Reverse Recovery Charge	Q_{rr}	-	88	-	nC	
Peak Reverse Recovery Current	I_{RRM}	-	5	-	A	

Typical Performance Characteristics

Fig 1: Output Characteristics $T_j=25^{\circ}\text{C}$

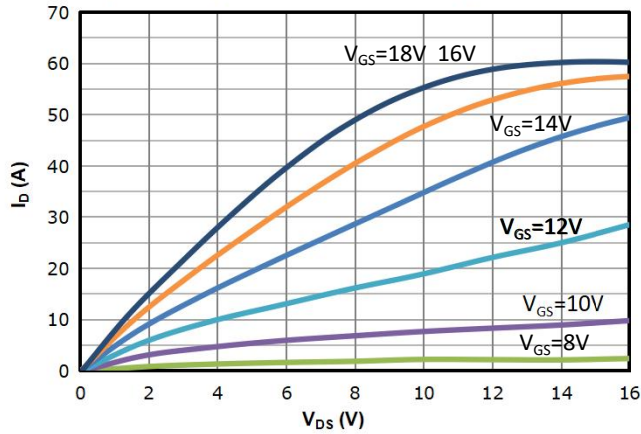


Fig 2: Output Characteristics $T_j=175^{\circ}\text{C}$

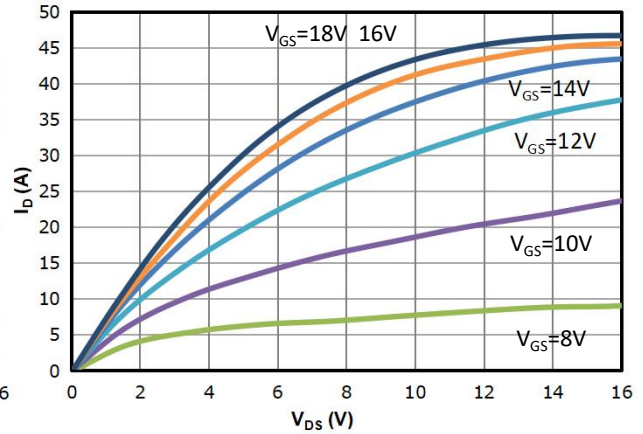


Fig 3: Transfer Characteristics

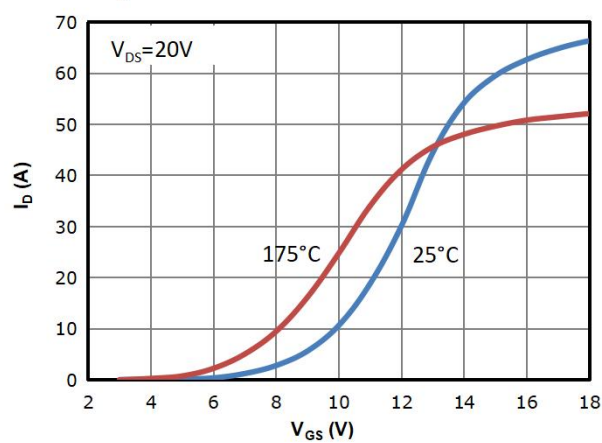


Fig 4: $R_{ds(on)}$ vs Drain Current and Gate Voltage

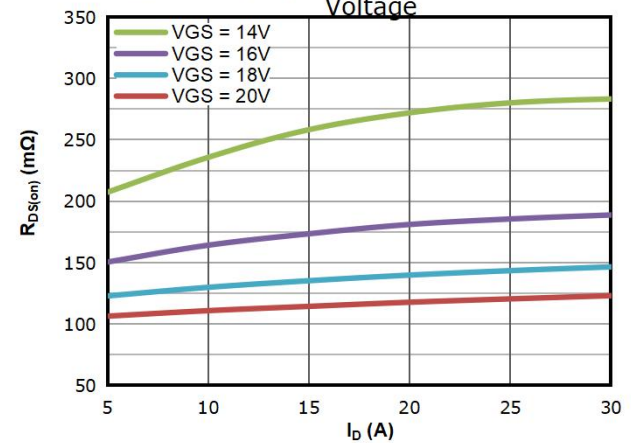


Fig 5: $R_{ds(on)}$ vs. Temperature

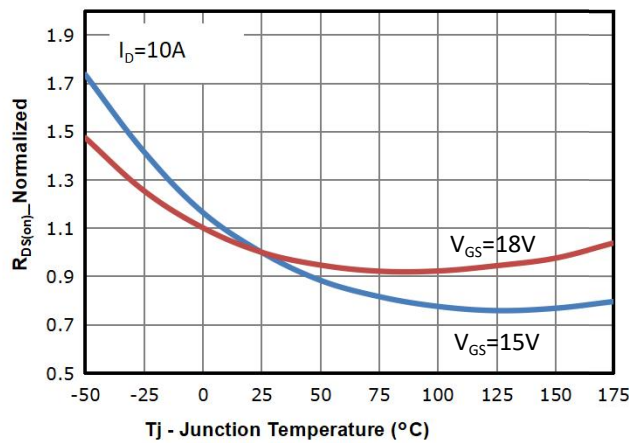


Fig 6: $V_{gs(th)}$ vs. Temperature

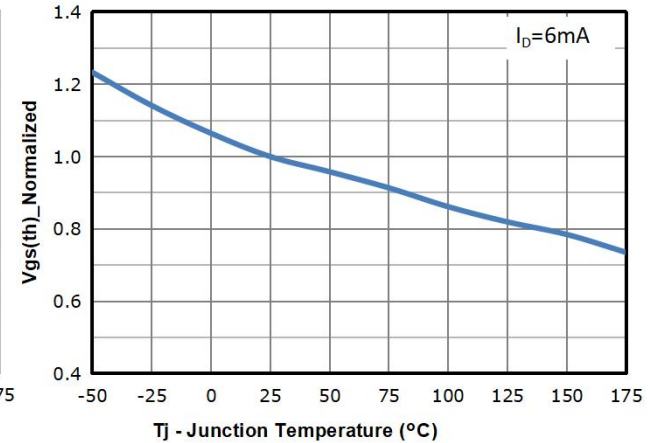


Fig 7: BVdss vs. Temperature

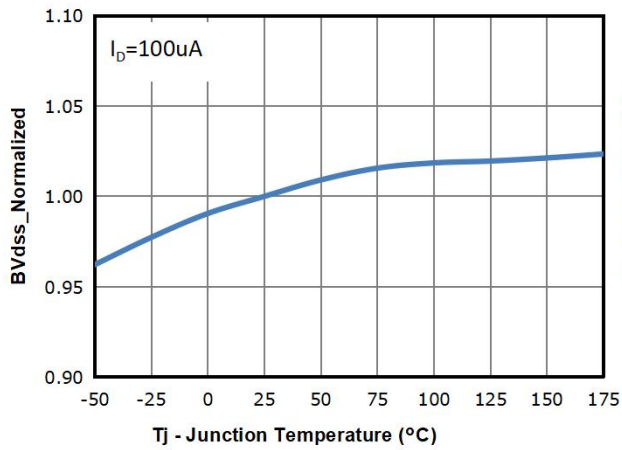


Fig 8: Capacitance Characteristics

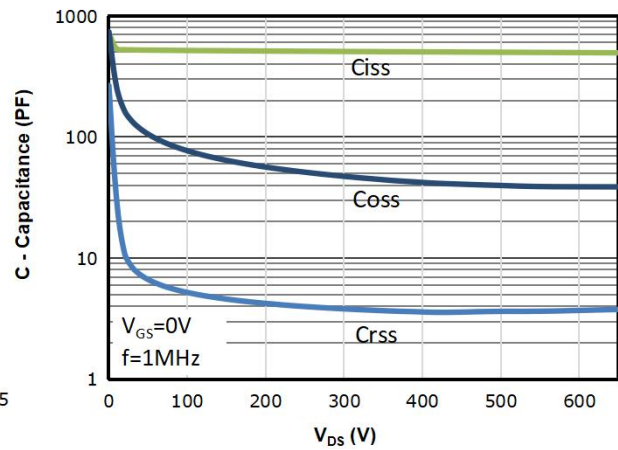


Fig 9: Gate Charge Characteristics

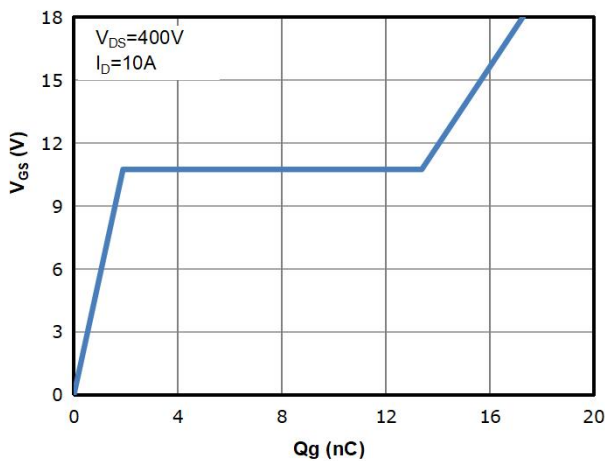


Fig 10: Body-diode Forward Characteristics

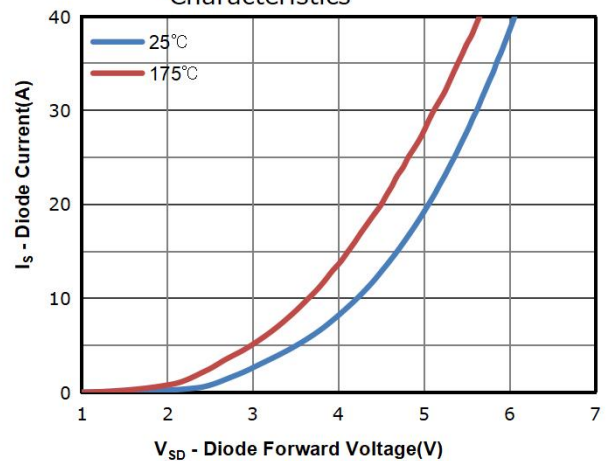


Fig 11: Power Dissipation

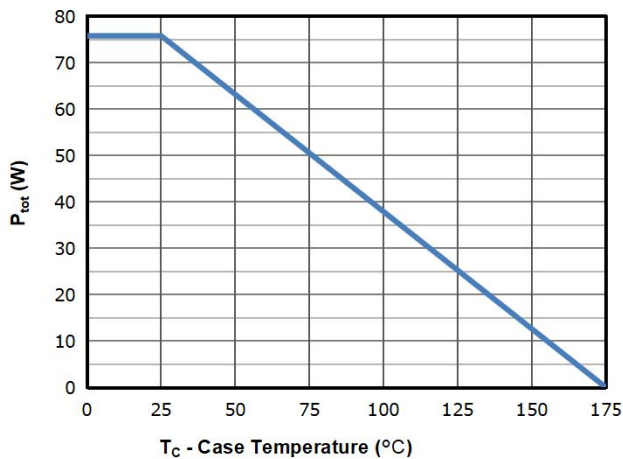


Fig 12: Drain Current Derating

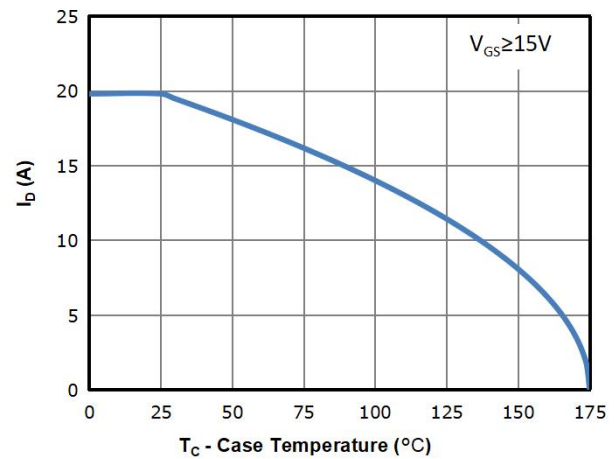




Fig 13: Safe Operating Area

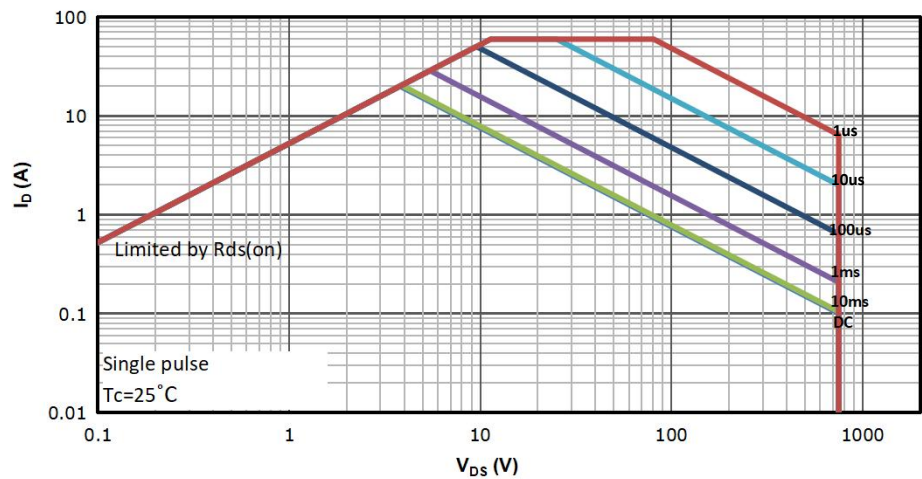
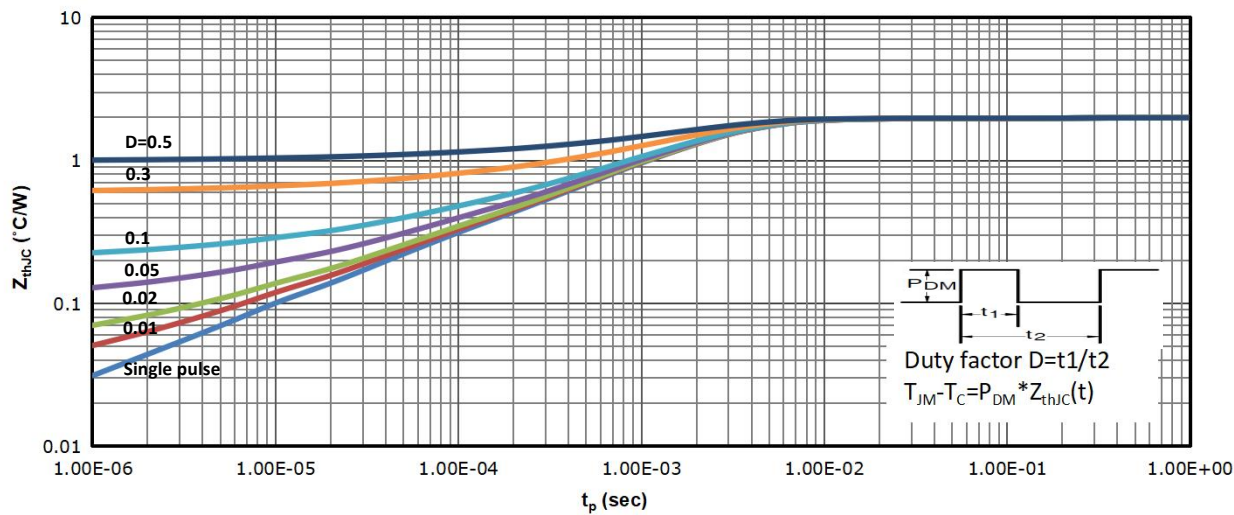
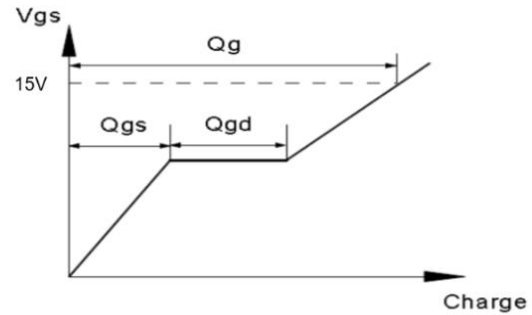
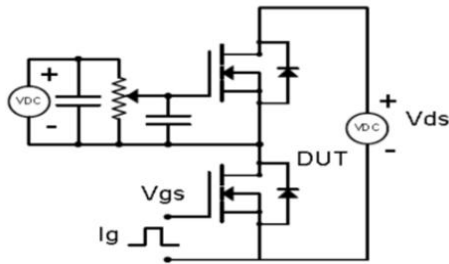


Fig 14: Max. Transient Thermal Impedance

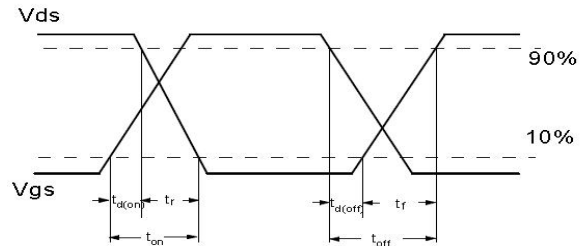
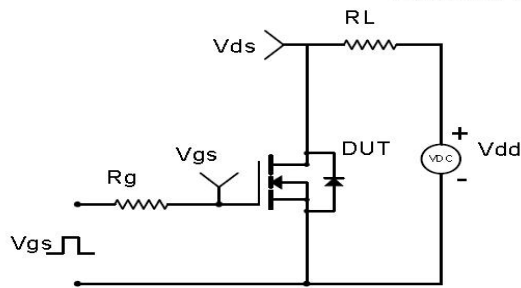


Test Circuit & Waveform

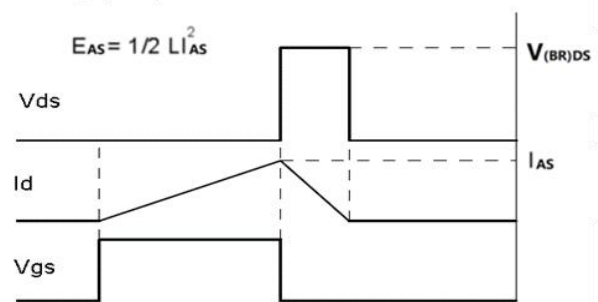
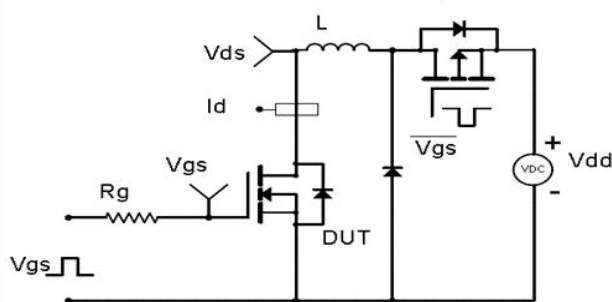
Gate Charge Test Circuit & Waveform



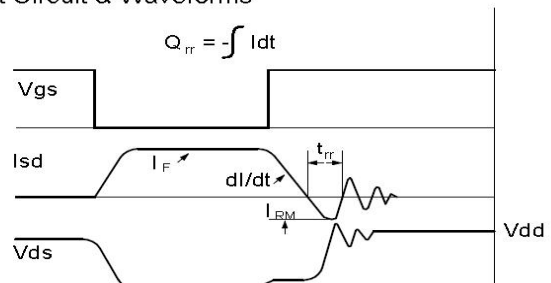
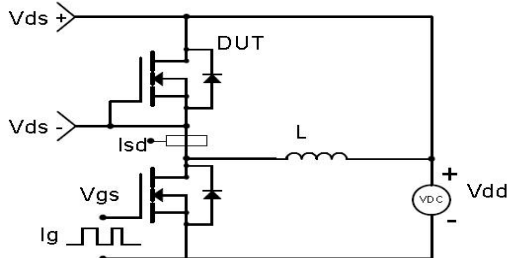
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



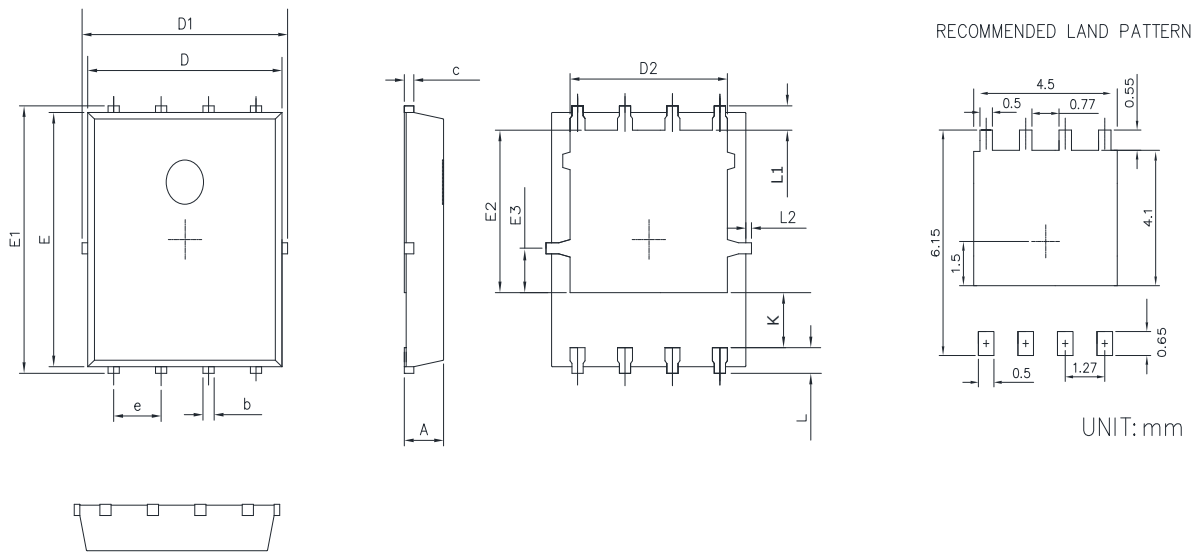
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Package Outline: PDFN5*6



SYMBOL	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.90	1.10	0.035	0.043
b	0.25	0.50	0.010	0.020
c	0.10	0.30	0.004	0.012
D	4.80	5.30	0.189	0.209
D1	4.90	5.50	0.193	0.217
D2	3.92	4.20	0.154	0.165
E	5.65	5.85	0.222	0.230
E1	5.90	6.20	0.232	0.244
E2	3.33	3.78	0.131	0.149
E3	0.80	1.00	0.031	0.039
e	1.27		0.050	
L	0.40	0.70	0.016	0.028
L1	0.65		0.026	
L2	0.00	0.15	0.000	0.006
K	1.00	1.50	0.039	0.059

Disclaimer

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